

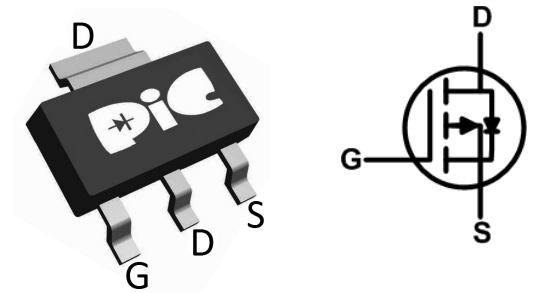
➤ General Description

This PAP84TB73QB P-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology
- SOT-223 package design

➤ SOT-223



➤ Application

- Motor and Load Control
- Power Management in White LED System
- Push Pull Converter
- LCD TV Inverter & AD/DC Inverter Systems.

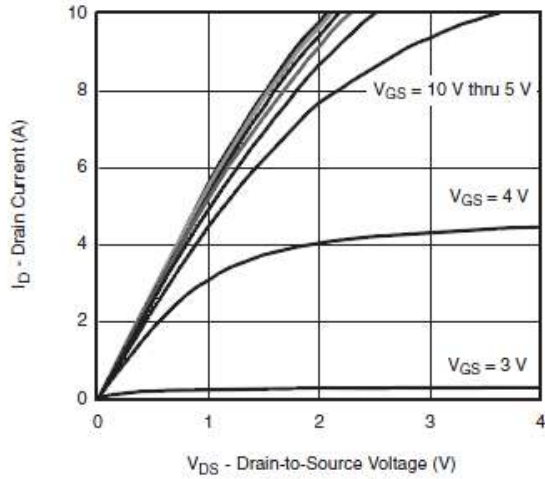
➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-60	V
Gate –Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current($T_J=150^\circ C$)	I_D	$T_A=25^\circ C$	-4.8
		$T_A=70^\circ C$	-3.6
Pulsed Drain Current	I_{DM}	-10	A
Continuous Source Current(Diode Conduction)	I_S	-1.6	A
Power Dissipation	P_D	$T_A=25^\circ C$	2.8
		$T_A=70^\circ C$	1.2
Operating Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{STG}	-55/150	$^\circ C$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^\circ C/W$

➤ Electrical Characteristics ($T_J=25^\circ C$ Unless otherwise noted)

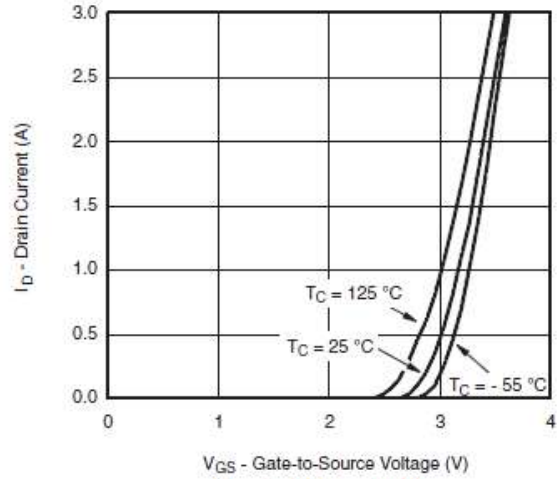
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0		-2.0	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-48V, V_{GS}=0V$			-1	uA
		$V_{DS}=-48V, V_{GS}=0V$ $T_J=85^\circ C$			-30	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \leq -5V, V_{GS}=-10V$	-5			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-4.8A$		125	135	m Ω
		$V_{GS}=-4.5V, I_D=-3.6A$		135	155	
Forward Transconductance	g_{FS}	$V_{DS}=-15V, I_D=-2.2A$		5		S
Diode Forward Voltage	V_{SD}	$I_S=-1.5A, V_{GS}=0V$		-0.75	-1.3	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=-30V, V_{GS}=-4.5V$ $I_D=-2.2A$		5	10	nC
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			2.5		
Input Capacitance	C_{iss}	$V_{DS}=-30V, V_{GS}=0V$ $f=1MHz$		410		pF
Output Capacitance	C_{oss}			45		
Reverse Transfer Capacitance	C_{riss}			20		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-30V, R_L=16.7\Omega$ $I_D=-1.8A, V_{GEN}=-10V$ $R_G=1\Omega$		5	10	ns
	t_r			15	25	
Turn-Off Time	$t_{d(off)}$			20	35	
	t_f		10	20		

➤ Typical Characteristics



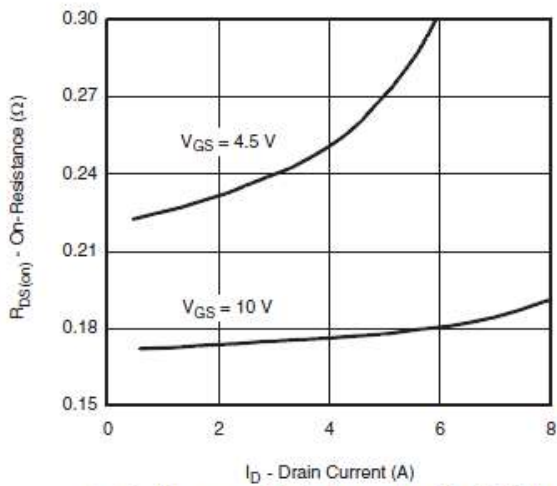
$V_{GS} = 10$ V thru 5 V

Output Characteristics

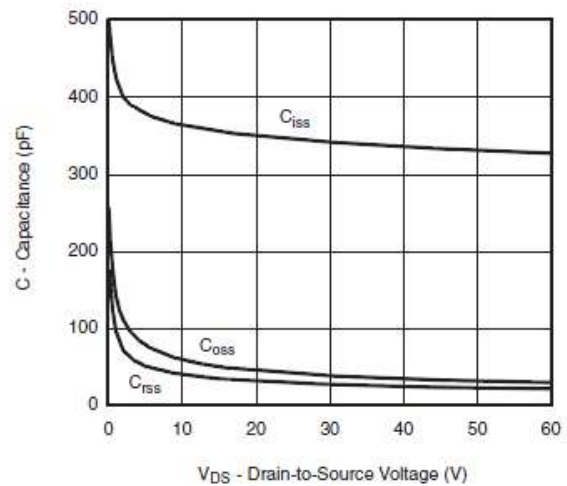


$T_C = 125^\circ C$

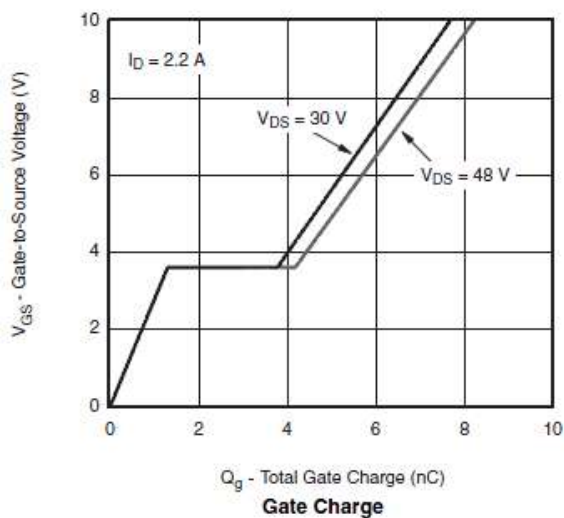
Transfer Characteristics



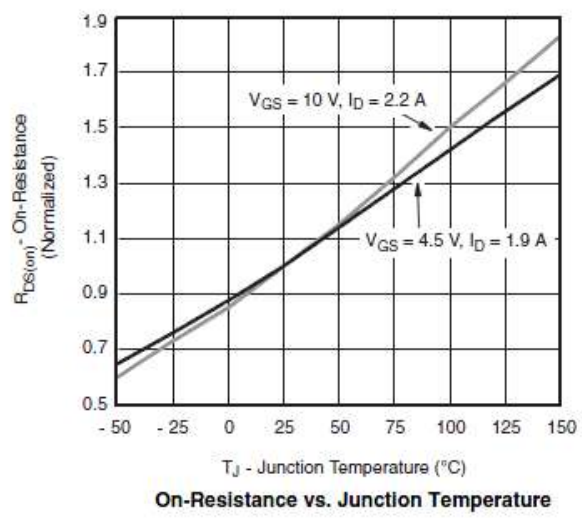
On-Resistance vs. Drain Current and Gate Voltage



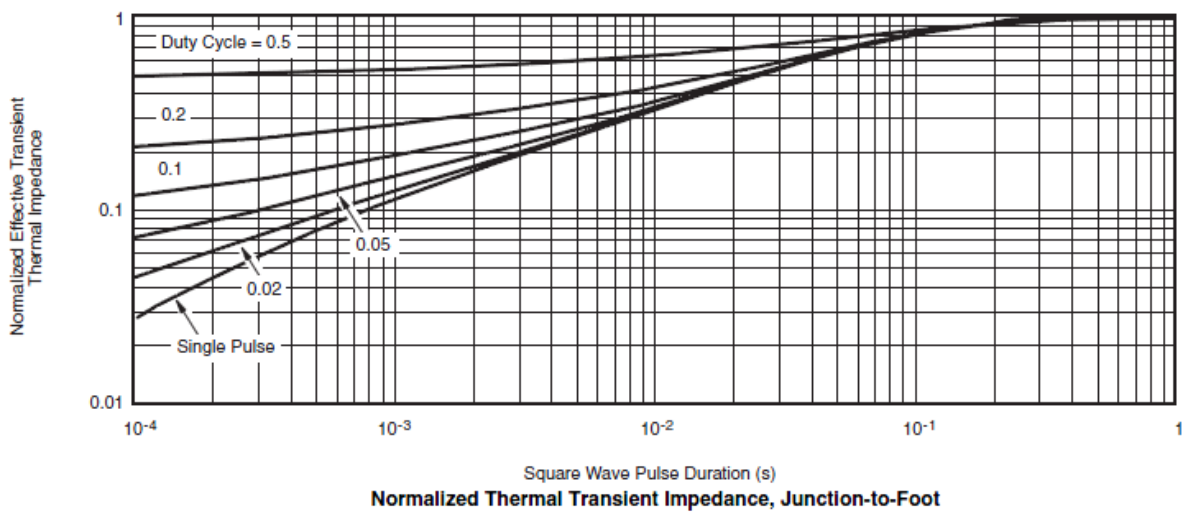
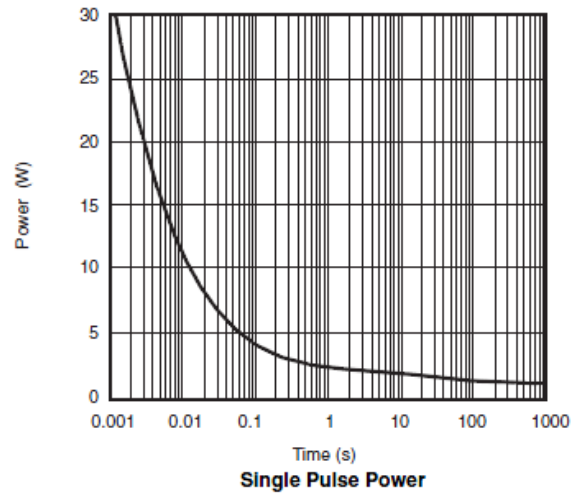
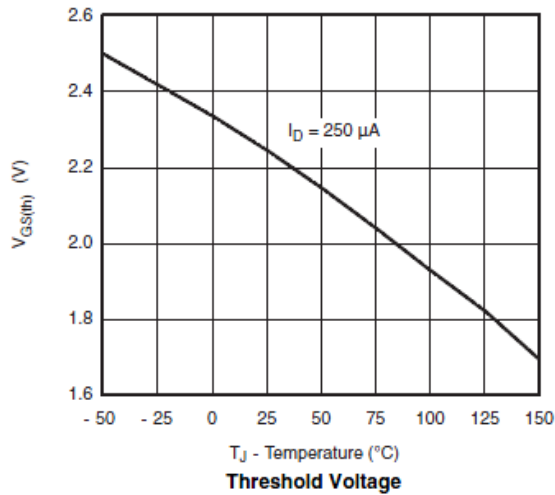
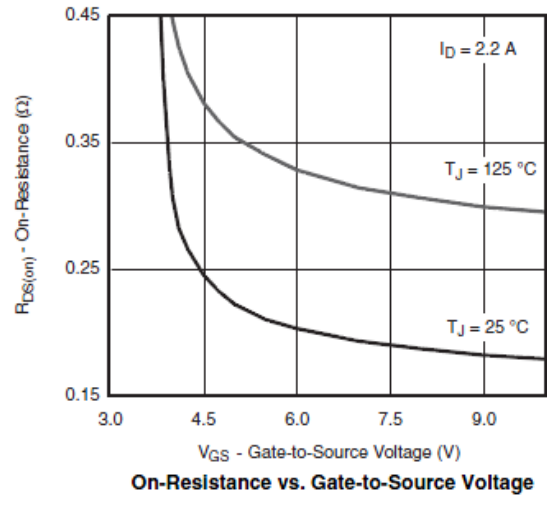
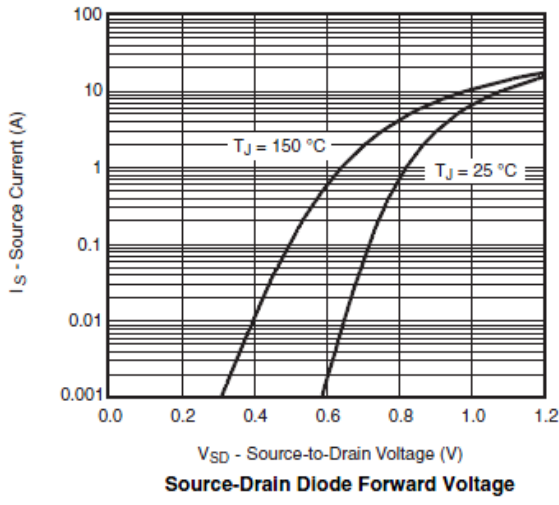
Capacitance



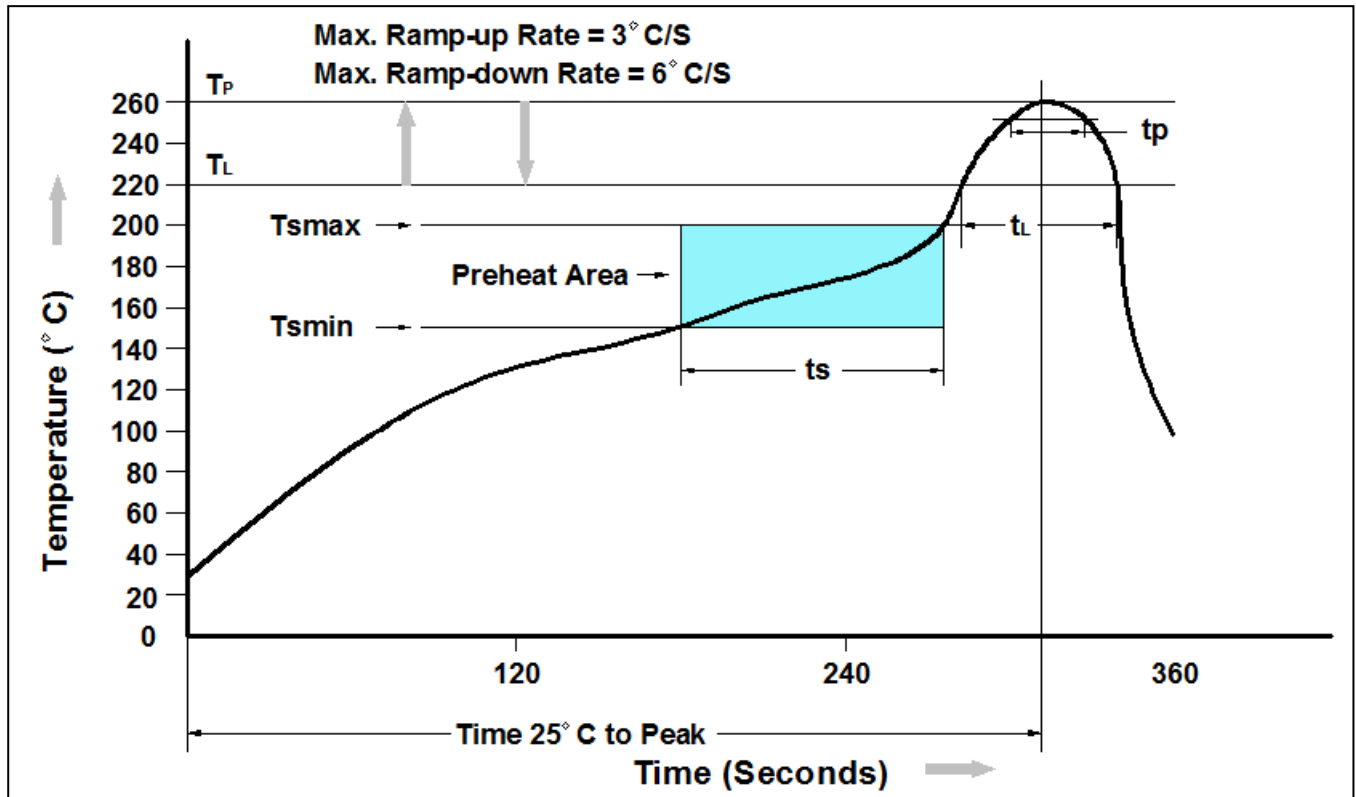
Gate Charge



On-Resistance vs. Junction Temperature



➤ Recommand IR Reflow Soldering Thermal Profile

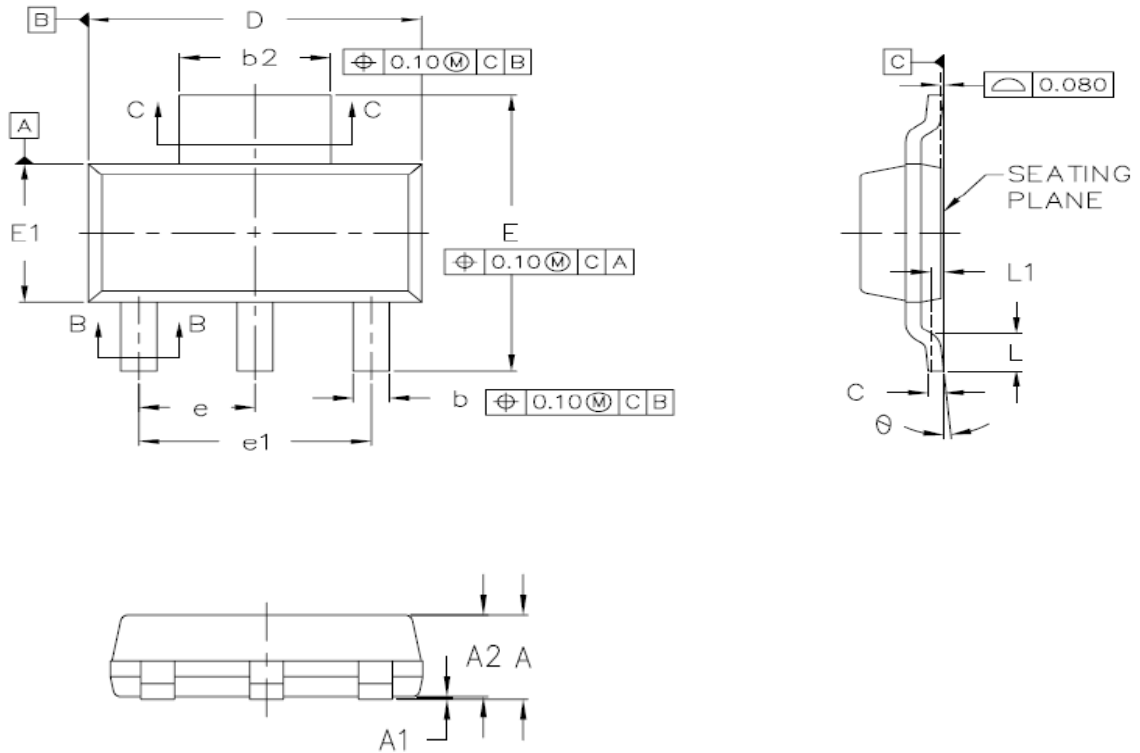


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	150°C
Temperature Max. (T _{smax})	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds
Average Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAP84TB73QB	SOT-223 Reel	2500 pcs

➤ Package Information (SOT-223)



DIMENSIONS	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	—	1.80	—	0.071
A1	0.02	0.10	0.001	0.004
A2	1.50	1.70	0.059	0.067
b	0.66	0.84	0.026	0.033
b1	0.60	0.79	0.024	0.031
b2	2.90	3.10	0.114	0.122
b3	2.84	3.05	0.112	0.120
c	0.23	0.35	0.009	0.014
c1	0.23	0.33	0.009	0.013
D	6.30	6.70	0.248	0.264
E	6.70	7.30	0.264	0.287
E1	3.30	3.70	0.130	0.146
e	2.30 BSC.		0.091 BSC.	
e1	4.60 BSC.		0.182 BSC.	
L	0.81	—	0.032	—
L1	0.25 BSC.		0.010 BSC.	
θ	0°	10°	0°	10°

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